CLAIMS

1. A ceramic board for semiconductor manufacture apparatuses comprising a ceramic substrate and a semiconductor wafer directly mounted thereon or indirectly supported at a fixed distance from its surface,

wherein the surface of said ceramic substrate, where said semiconductor wafer is to be mounted or supported, is controlled to a flatness of 1 to 50 μm over a measurement range of [(diametric end-to-end length) - 10 mm].

2. A ceramic board for semiconductor manufacture apparatuses comprising a ceramic substrate and a conductor layer disposed internally or on a surface thereof,

wherein said surface is controlled to a flatness of 1 to 50 μm over a measurement range of [(diametric end-to-end length) - 10 mm].

3. The ceramic board according to Claim 1 or 2

wherein said ceramic substrate is in the form of a disk with a diameter in excess of 150 mm.

4. The ceramic board for semiconductor manufacture apparatuses according to Claim 1, 2 or 3

wherein said ceramic substrate comprises aluminum nitride.

5. The ceramic board for semiconductor manufacture apparatuses according to any of Claims 1 to 4

wherein said ceramic substrate contains more than 50 weight % of aluminum nitride.

6. The ceramic board for semiconductor manufacture apparatuses according to any of Claims 2 to 5

wherein the conductor layer disposed internally of said

ceramic substrate is formed as at least one layer in the center in thickness direction thereof or in an offset position displaced from said center toward the surface thereof,

said surface being opposite to the surface where a semiconductor wafer is to be mounted or supported.

7. The ceramic board for semiconductor manufacture apparatuses according to any of Claims 2 to 5

wherein the conductor layer is formed on the surface of said ceramic substrate,

said surface being opposite to the surface where a semiconductor wafer is to be mounted or supported.

8. The ceramic board for semiconductor manufacture apparatuses according to any of Claims 2 to 5 further comprising

a conductor layer formed on a surface of said ceramic substrate and

a semiconductor wafer mounted on said conductor layer,

said ceramic substrate functioning as a wafer prover.

9. The ceramic board for semiconductor manufacture apparatuses according to any of Claims 2 to 5

wherein the conductor layer disposed internally of said ceramic substrate comprises at least one layer formed in an offset position displaced from the center in thickness direction thereof toward the surface where a semiconductor wafer is to be mounted or supported.